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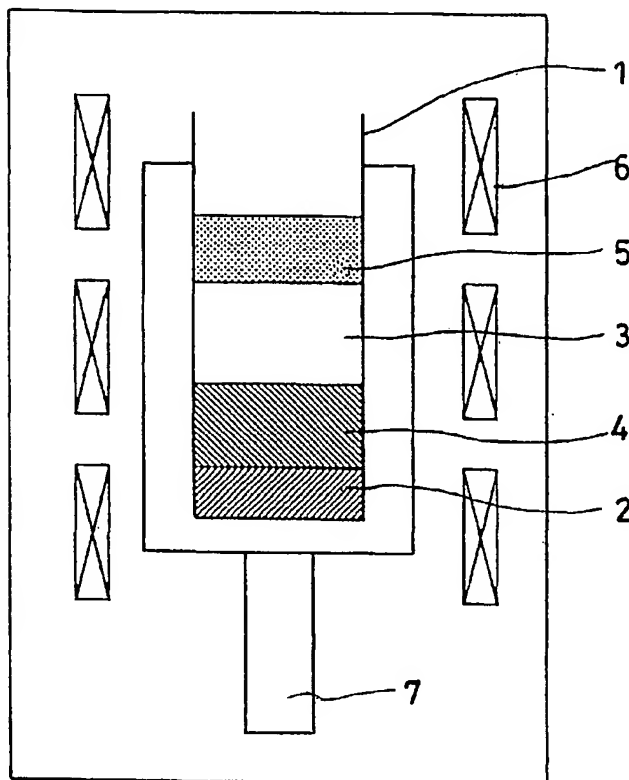
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(54) Title: InP SINGLE CRYSTAL, GaAs SINGLE CRYSTAL, AND METHOD FOR PRODUCTION THEREOF



(57) Abstract: A method for the production of an InP single crystal includes gradually cooling a molten raw material held in contact with a seed crystal to solidify the molten raw material from a lower part toward an upper part of an interior of a crucible and grow a single crystal, causing the seed crystal to possess an average dislocation density of less than 10000/cm² and assume substantially identical cross-sectional shape and size with a crosssectional shape and size of a single crystal to be grown, and allowing the InP single crystal to be grown to retain a non-doped state or a state doped with Fe or Sn.

WO 2005/007939 A1



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